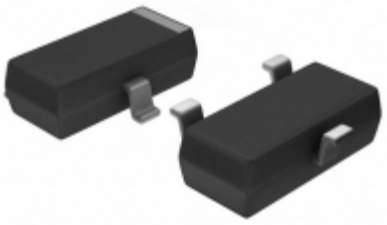




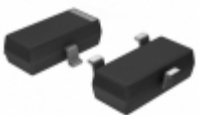



	<p><b>SI2315BDS-T1-GE3</b></p>
	<p><b>Hersteller-Teilenummer:</b> <a href="#">SI2315BDS-T1-GE3</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a></p> <p><b>Teil der Beschreibung:</b> MOSFET P-CH 12V 3A SOT23-3</p> <p><b>Datenblätter:</b>  <a href="#">SI2315BDS-T1-GE3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 48307 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	<a href="#">SI2315BDS-T1-GE3</a>
Hersteller	<a href="#">Vishay / Siliconix</a>
Beschreibung	MOSFET P-CH 12V 3A SOT23-3
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	48307 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-236-3, SC-59, SOT-23-3
Supplier Device-Gehäuse	SOT-23-3 (TO-236)
Verlustleistung (max)	750mW (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3A (Ta)
Rds On (Max) @ Id, Vgs	50 mOhm @ 3.85A, 4.5V
VGS (th) (Max) @ Id	900mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	15nC @ 4.5V
Eingabekapazität (Ciss) (Max) @ Vds	715pF @ 6V
Antriebsspannung (Max Rds On, Min Rds On)	4.5V
Vgs (Max)	±8V
Verpackung	Tape & Reel (TR)

SI2315BDS-T1-GE3 ist neu im Original, Suche SI2315BDS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2315BDS-T1-GE3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI2315BDS-T1-GE3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <b>SI2315DS-T1-GE3</b> VISHAY SI2315DS-T1-GE3 VISHAY	 <b>SI2315DS</b> 89K SI2315DS 89K	 <b>SI2315DS-T1-E3</b> VISHAY SI2315DS-T1-E3 VISHAY	 <b>SI2315BDS-T1-GE3</b> Electro-Films (EF1) / Vishay MOSFET P-CH 12V 3A SOT23-3
 <b>SI2315BDS-T1-E3</b> Vishay / Siliconix MOSFET P-CH 12V 3A SOT23-3	 <b>SI2315BDS-T1</b> VISHAY VISHAY 1253+	 <b>SI2315DS-T1</b> VISHAY SI2315DS-T1 VISHAY	 <b>SI2315BDS</b> KEXIN SI2315BDS KEXIN

### heiße Teile

Mehr

 SI2312BDS-T1-E3	 SI2312BDS-T1-GE3	 SI2312BDS-T1-GE3	 SI2312CDS-T1-E3	 SI2312CDS-T1-GE3
 SI2312CDS-T1-GE3	 SI2312DS	 SI2312DS-T1	 SI2312DS-T1-E3	 SI2312DS-T1-GE3
 SI2313DS	 SI2313DS-T1-E3	 SI2313DS-T1-GE3	 SI2314DS	 SI2314DS-T1-E3
 SI2314DS-T1-GE3	 SI2314EDS	 SI2314EDS-T1-E3	 SI2314EDS-T1-E3	 SI2314EDS-T1-GE3
 SI2314EDS-T1-GE3	 SI2315BDS	 SI2315BDS-T1-E3	 SI2315BDS-T1-E3	 SI2315BDS-T1-GE3
 SI2315DS	 SI2315DS-T1	 SI2315DS-T1-E3	 SI2315DS-T1-GE3	 SI2316-DS
 SI2316BDS-T1-E3	 SI2316BDS-T1-E3	 SI2316BDS-T1-GE3	 SI2316BDS-T1-GE3	 SI2316DS
 SI2316DS-T1-E3	 SI2316DS-T1-E3	 SI2316DS-T1-GE3	 SI2316DS-T1-GE3	 SI2317DS
 SI2317DS-T1-E3	 SI2318ADS-T1-GE3	 SI2318BDS-T1-E3	 SI2318BDS-T1-GE3	 SI2318CDS-T1-E3
 SI2318CDS-T1-GE3	 SI2318CDS-T1-GE3	 SI2318DS	 SI2318DS-T1-E3	 SI2318DS-T1-E3

Contact us: [Info@Y-IC.com](mailto:Info@Y-IC.com)

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